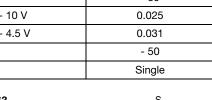
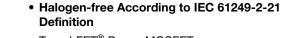


Vishay Siliconix

Automotive P-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	- 80				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.025				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.031				
I _D (A)	- 50				
Configuration	Single				



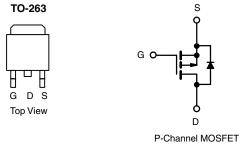


FEATURES



- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- Compliant to RoHS Directive 2002/95/EC





ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM50P08-25L-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 80		
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C ^a	1	- 50		
	T _C = 125 °C	l _D	- 30		
Continuous Source Current (Diode Conduction) ^a	Is	- 50	Α		
Pulsed Drain Current ^b	I _{DM}	- 120			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 47		
Single Pulse Avalanche Energy	L = 0.1 IIIH	E _{AS}	110	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	T _C = 25 °C	150	W	
	T _C = 125 °C	P_{D}	50	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	1	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

SQM50P08-25L

Vishay Siliconix



SPECIFICATIONS ($T_C = 25 ^{\circ}C_{\odot}$, unless otherv	vise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} =	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		- 2.0	- 2.5		
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = - 80 V	-	-	- 1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 80 V, T _J = 125 °C	-	-	- 50	μΑ	
		$V_{GS} = 0 V$	V _{DS} = - 80 V, T _J = 175 °C	-	-	- 250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≤ - 5 V	- 50	-	-	Α	
		V _{GS} = - 10 V	I _D = - 12.5 A	-	0.020	0.025	Ω	
Dunin Course On State Registeres	Б	V _{GS} = - 10 V	I _D = - 12.5 A, T _J = 125 °C	-	-	0.044		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 12.5 A, T _J = 175 °C	-	-	0.055		
		V _{GS} = - 4.5 V	I _D = - 10.5 A	-	0.025	0.031		
Forward Transconductance ^b	9 _{fs}	V _{DS} =	· 15 V, I _D = - 12.5 A	-	36	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		V _{DS} = - 25 V, f = 1 MHz	-	4280	5350	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	356	445		
Reverse Transfer Capacitance	C _{rss}			-	240	300		
Total Gate Charge ^c	Qg			-	91	137		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -40 \text{ V}, I_{D} = -12.5 \text{ A}$	-	8.2	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	24	-		
Turn-On Delay Time ^c	t _{d(on)}				11	17		
Rise Time ^c	t _r	$V_{DD} = -40 \text{ V}, R_L = 3.2 \Omega$ $I_D \cong -12.5 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		-	11	17	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	71	107		
Fall Time ^c	t _f			-	16	24		
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed Current ^a	I _{SM}			-	-	- 120	Α	
Forward Voltage	V_{SD}	I _F =	1	- 0.86	- 1.5	V		

Notes

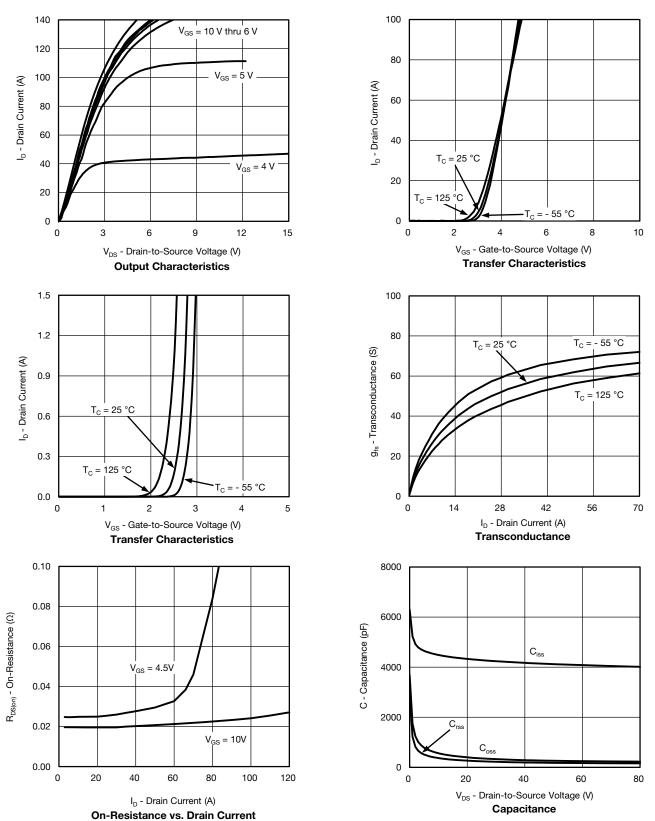
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





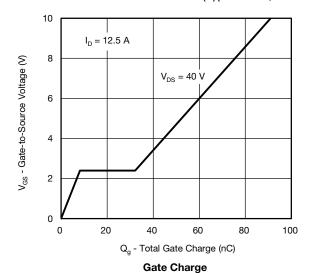
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

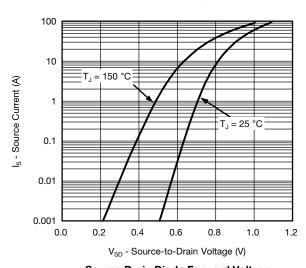


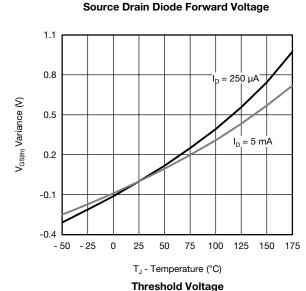
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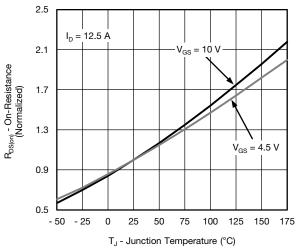


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

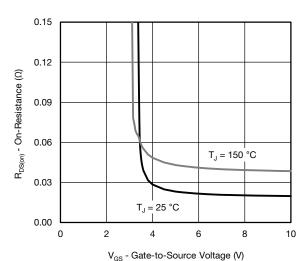




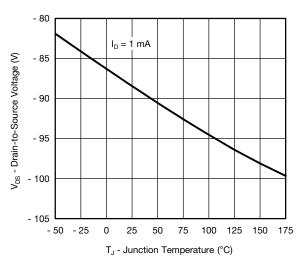




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

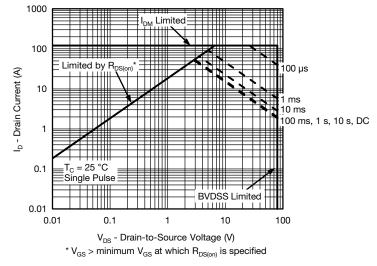


Drain Source Breakdown vs. Junction Temperature

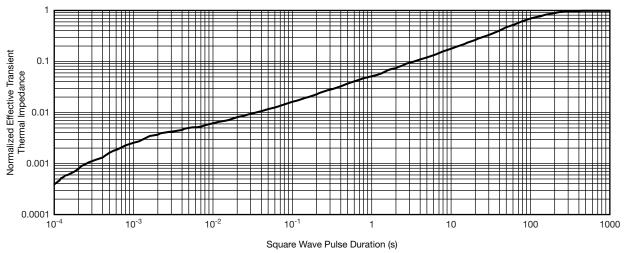




THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Safe Operating Area

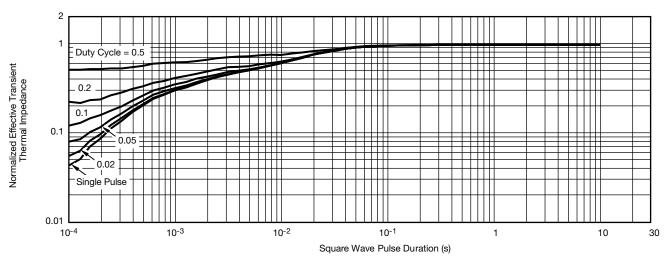


Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

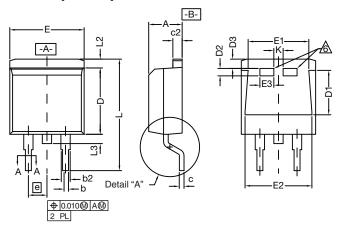
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

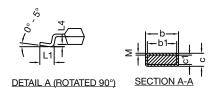
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TO-263 (D²PAK): 3-LEAD





		INCHES		MILLIN	METERS	
DIM.		MIN.	MAX.	MIN.	MAX.	
А		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
	Thin lead	0.013	0.017	0.330	0.431	
c1	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
D1		0.220	0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
	Е	0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	-	
	E2	0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
	е	0.100 BSC		2.54 BSC		
	K	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
М		-	0.002	-	0.050	
ECN: T10-0738-Rev. J, 03-Jan-11 DWG: 5843						

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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